

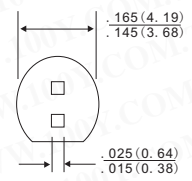
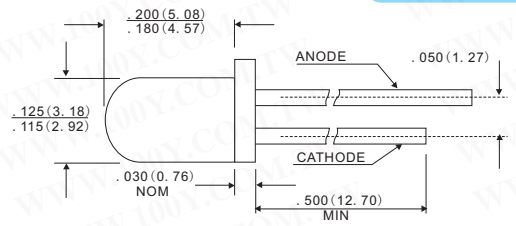


OPTOELECTRONICS & INDICATORS

the Most Recent Electronic Catalogue 2007

Infrared Emitting Diode

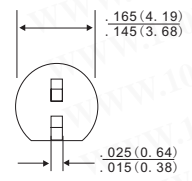
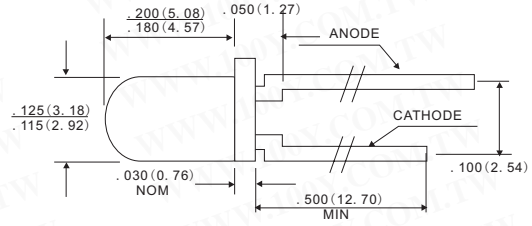
Detailed product specifications are available on: us.100y.com.tw



Features

- Narrow irradiance pattern
- Mechanically and spectrally matched to the Op505 and Op535 series devices
- Variety of power ranges
- Small package size for space limited applications
- T-1 package style

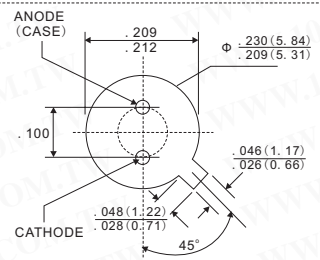
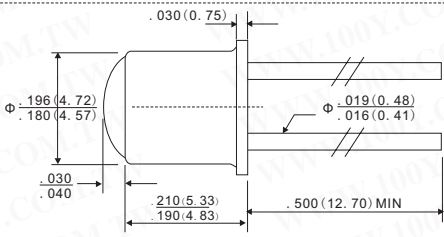
Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	Vf@If(mA)	λP(nm)	Δθ(deg)	If max.	Vr max.
32541	OP165A	OPTEK	GaAs Platic Infrared Emitting Diode	T-1	0.5mW	1.6V/100mA	935	18	50mA	2V
36281	OP165B	OPTEK	Infrared Emitting Diodes(GaGIAs)	T-1	0.5mW	1.6V/100mA	935	18	50mA	2V
36282	OP165C	OPTEK	Infrared Emitting Diodes(GaGIAs)	T-1	0.5mW	1.6V/100mA	935	18	50mA	2V
36284	OP165D	OPTEK	Infrared Emitting Diodes(GaGIAs)	T-1	0.5mW	1.6V/100mA	935	18	50mA	2V



Features

- Narrow irradiance pattern
- Mechanically and spectrally matched to the Op506 series phototransistors
- Variety of power ranges
- Small package size for space limited applications
- T-1 package style

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	Vf@If(mA)	λP(nm)	Δθ(deg)	If max.	Vr max.
40932	OP166A	OPTEK	Infrared Emitting Diodes(GaGIAs)	T-1 3/4	100mW	20mA	935nm	18deg	20mA	2V



FEATURES

- Enhanced temperature range
- To-46 hermetically sealed package
- Mechanically and spectrally matched to Op800 OP593, and Op598 phototransistors
- Specified apertured power in ranges to satisfy most applications
- Variety of power ranges

DESCRIPTION

The Op231 series devices are gallium aluminum arsenide infrared emitting diodes mounted in hermetic TO-46 housings. Gallium aluminum arsenide features higher radiated output than gallium arsenide at the same forward current. The wavelength is centered at 890nm which closely matches the spectral response of silicon phototransistors. The Op231 series is lensed to provide a narrow beam angle (18° between half power points). The narrow beam angle and the specified radiant intensity of the Op231 series allow ease of design in beam interrupt applications in conjunction with the Op800 or Op598 photosensor.

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
36469	OP232	OPTEK	GaAlAs Hermetic Infrared Emitting Diode	TO-46	200mW	890nm	±18deg	5A	5V



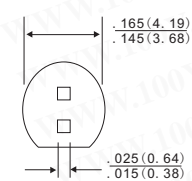
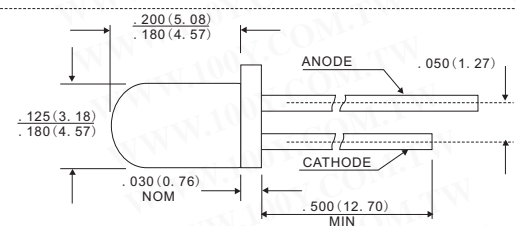
FEATURES

- Wide irradiance pattern
- Enhanced temperature range
- Mechanically and spectrally matched to the OP800WSL and OP830SL series devices
- Significantly higher power output than GaAs at equivalent drive currents
- TO-46 hermetically sealed package

DESCRIPTION

The Op231 W series devices are 890nm gallium aluminum arsenide infrared emitting diodes mounted in hermetically sealed packages. The broad irradiance pattern provides relatively even illumination over a large area.

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	If max.	Vr max.
36470	OP232W	OPTEK	GaAlAs Hermetic Infrared Emitting Diode	TO-46	200mW	890nm	100mA	2V



Features

- Narrow irradiance pattern
- Mechanically and spectrally matched to the Op505 and Op535 series devices
- Significantly higher power output than GaAs at equivalent drive currents
- Wavelength matched to silicon's peak response
- T-1 package style

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
36428	OP265A	OPTEK	Infrared Emitting Diodes(GaGIAs)	T-1	100mW	890nm	±18 deg	50mA	2V



T E L : Taiwan: 886-3-5753170
 F A X : Taiwan: 886-3-5729594
 E-mail : Taiwan: us_sale@100y.com.tw

Shenzhen: 86-755-83298787
 Shenzhen: 86-755-83640655
 Shenzhen: 100y@163.com

Shanghai: 86-21-54151736
 Shanghai: 86-21-64605107
 Shanghai: 100y-1@163.com